

# 4V Drive Pch+Pch MOSFET

#### **SH8J65**

#### Structure

Silicon P-channel MOSFET

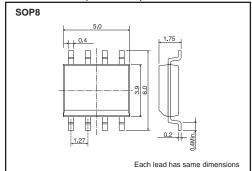
#### ● Features

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

#### Application

Switching

#### ●Dimensions (Unit:mm)



### Packaging specifications

	Package	Taping
Type	Code	TB
	Basic ordering unit (pieces)	2500
SH8J65		0

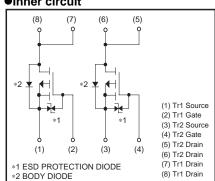
#### ●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

Parameter		Symbol		Limits	Unit	
Drain-source voltage		VDSS		-30	V	
Gate-source voltage		V <sub>GSS</sub>		±20	V	
Desir success	Continuous	I <sub>D</sub>		±7.0	А	
Drain current	Pulsed	I <sub>DP</sub>	*1	±28	A	
Source current	Continuous	Is		-1.6	A	
(Body diode)	Pulsed	I <sub>SP</sub>	*1	-28	A	
Total power dissipation		Pp	*2	2.0	W / TOTAL	
		10		1.4	W / ELEMENT	
Channel temperature		Tch		150	°C	
Range of Storage temperature		Tstg		-55 to +150	°C	

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board

#### ●Inner circuit



**SH8J65 Data Sheet** 

●Electrical characteristics (Ta=25°C) <It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	-	_	±10	μА	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	-30	-	-	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	-1	μА	Vps= -30V, Vgs=0V
Gate threshold voltage	V <sub>GS (th)</sub>	-1.0	_	-2.5	V	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA
Static drain-source on-state resistance	R <sub>DS</sub> (on)	-	21.5	29.0	mΩ	I <sub>D</sub> = -7A, V <sub>G</sub> S= -10V
		_	29.0	39.0	mΩ	I <sub>D</sub> = -3.5A, V <sub>G</sub> S= -4.5V *
		_	31.0	40.8	mΩ	I <sub>D</sub> = -3.5A, V <sub>G</sub> s= -4.0V *
Forward transfer admittance	Y <sub>fs</sub> *	6.0	_	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -7A *
Input capacitance	Ciss	-	1200	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	-	170	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	170	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	12	_	ns	Vpp≒-15V
Rise time	tr *	-	40	_	ns	ID= -3.5A
Turn-off delay time	td (off) *	-	80	_	ns	$V_{GS} = -10V$ $R_{L} = 4.3\Omega$
Fall time	t <sub>f</sub> *	_	65	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	18	-	nC	Vpp≒15V
Gate-source charge	Q <sub>gs</sub> *	_	3.5	-	nC	I <sub>D</sub> = -7A   V <sub>G</sub> s= -5V
Gate-drain charge	Q <sub>gd</sub> *		6.5	_	nC	$R_L=2.1\Omega / R_G=10\Omega$

<sup>\*</sup>Pulsed

#### ●Body diode characteristics (Source-Drain) (Ta=25°C)

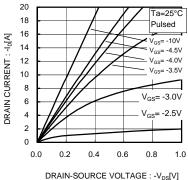
<It is the same characteristics for the Tr1 and Tr2.>

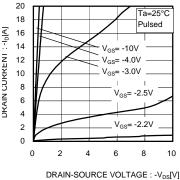
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	-1.2	V	Is= -7A, Vgs=0V

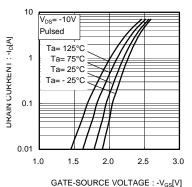
<sup>\*</sup>Pulsed

SH8J65 Data Sheet

#### •Electrical characteristic curves



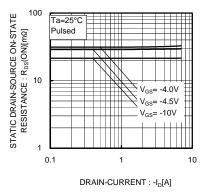


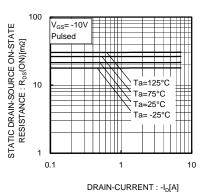


DRAIN-SOURCE VOLTAGE : -V<sub>DS</sub>[V] Fig.1 Typical Output Characteristics( I )

DRAIN-SOURCE VOLTAGE : -V<sub>DS</sub>[V]
Fig.2 Typical Output Characteristics( II )

Fig.3 Typical Transfer Characteristics





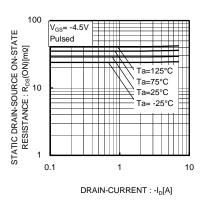
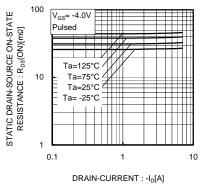
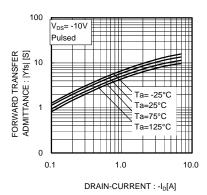


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )

Fig.6 Static Drain-Source On-State
Resistance vs. Drain Current(Ⅲ)





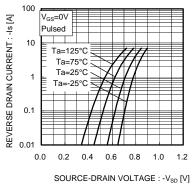
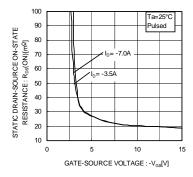


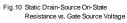
Fig.7 Static Drain-Source On-State
Resistance vs. Drain Current(IV)

Fig.8 Forward Transfer Admittance vs. Drain Current

Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

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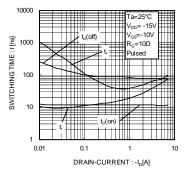


Fig.11 Switching Characteristics

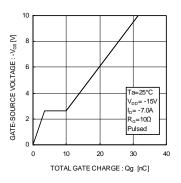


Fig.12 Dynamic Input Characteristics

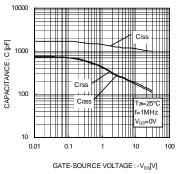


Fig.13 Typical Capacitance vs. Drain-Source Voltage

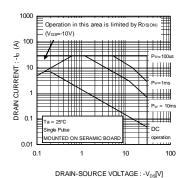


Fig.14 Maximum Safe Operating Aera

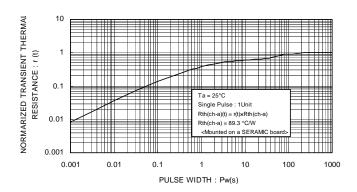


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

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#### Measurement circuits

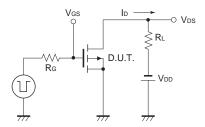


Fig.16 Switching Time Test Circuit

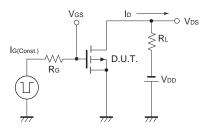


Fig.18 Gate Charge Test Circuit

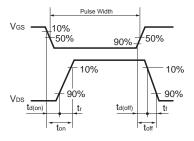


Fig.17 Switching Time Waveforms

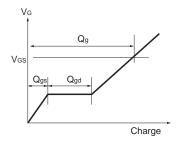


Fig.19 Gate Charge Waveform

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